

合肥中恒微半导体有限公司

HeFei Cpower Technology.,Ltd.

2B150ZF120S1P



➤ 产品外观 / Appearance



$V_{CES} = 1200V$

$I_{C\text{ nom}} = 150A / I_{CRM} = 300A$

➤ 特性 / Features

- | | |
|--------------------|--------------------------------------|
| A. 半桥结构 | A. Half-bridge Structure |
| B. 低开关损耗 | B. Low Switching Losses |
| C. 高速 NPT 结构的 IGBT | C. High Speed IGBT in NPT Technology |

➤ 用途 / Applications

- | | |
|-----------|---|
| A. 电机传动 | A. Motor Drives |
| B. 伺服驱动器 | B. Servo Drives |
| C. 高频开关应用 | C. High Frequency Switching Application |

➤ 相关信息 / Related Information

条形码 / Barcode Code



二维码 / DMX – Code



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IGBT, 逆变器 / IGBT, Inverter



最大额定值 / Maximum Rated Values

集电极-发射极电压 Collector-emitter voltage	$T_j = 25^\circ\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_{\text{C}} = 80^\circ\text{C}, T_{\text{j max}} = 150^\circ\text{C}$	$I_{\text{C nom}}$	150	A
集电极重复峰值电流 Repetitive peak collector current	$t_p = 1 \text{ ms}$	I_{CRM}	300	A
栅极-发射极峰值电压 Gate-emitter peak voltage		V_{GES}	± 20	V

特征值 / Characteristic Values

			Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-emitter saturation voltage	$I_{\text{C}} = 150 \text{ A}, V_{\text{GE}} = 15 \text{ V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	$V_{\text{CE sat}}$	3.1 3.8	3.4	V
栅极阈值电压 Gate threshold voltage	$I_{\text{C}} = 6 \text{ mA}, V_{\text{CE}} = V_{\text{GE}}, T_j = 25^\circ\text{C}$		V_{GETh}	5.0	5.8	6.5
栅极电荷/Gate charge	$V_{\text{GE}} = -15 \text{ V} \dots +15 \text{ V}$		Q_{G}	1.8		μC
内部栅极电阻 Internal gate resistor	$T_j = 25^\circ\text{C}$		R_{Gint}	1.3		Ω
输入电容/Input capacitance	$f = 1 \text{ MHz}, T_j = 25^\circ\text{C}, V_{\text{CE}} = 25 \text{ V}, V_{\text{GE}} = 0 \text{ V}$		C_{ies}	10		nF
反向传输电容 Reverse transfer capacitance			C_{res}	0.6		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{\text{CE}} = 1200 \text{ V}, V_{\text{GE}} = 0 \text{ V}, T_j = 25^\circ\text{C}$		I_{CES}		1.0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{\text{CE}} = 0 \text{ V}, V_{\text{GE}} = 20 \text{ V}, T_j = 25^\circ\text{C}$		I_{GES}		400	nA
开通延迟时间 Turn-on delay time	$I_{\text{C}} = 150 \text{ A}, V_{\text{CE}} = 600 \text{ V}$ $V_{\text{GE}} = \pm 15 \text{ V}$ $R_{\text{Gon}} = 5.1 \Omega$ $R_{\text{Goff}} = 2.5 \Omega$ Inductive Load	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	$t_{\text{d on}}$	70 90		ns
上升时间/Rise time		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	t_{r}	62 70		ns
关断延迟时间 Turn-off delay time		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	$t_{\text{d off}}$	253 286		ns
下降时间/Fall time		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	t_{f}	29 32		ns
开通损耗能量 Turn-on energy loss		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	E_{on}	15.4 21.3		mJ
关断损耗能量 Turn-off energy loss		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	E_{off}	3.8 5.7		mJ
短路数据/SC data	$V_{\text{GE}} \leq 15 \text{ V}, V_{\text{CC}} = 600 \text{ V}$ $t_p \leq 10 \mu\text{s}, T_j = 125^\circ\text{C}$		I_{SC}	1100		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0.11	K/W
在开关状态下温度 Temperature under switching			$T_{\text{j op}}$	-40	125	$^\circ\text{C}$

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二极管, 逆变器 / Diode, Inverter



最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_j = 25^\circ\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	150	A
正向重复峰值电流 Repetitive peak forward current	$t_p = 1 \text{ ms}$	I_{FRM}	300	A

特征值 / Characteristic Values

			Min.	Typ.	Max.	
正向电压/Forward voltage	$I_F = 150 \text{ A}, V_{GE} = 0 \text{ V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	V_F	1.9 1.9	2.1	V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 150 \text{ A}, V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$ $-di_F/dt = 1400 \text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	I_{RM}	145 162		A
恢复电荷/Recovered charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	Q_r	7.1 14.7		μC
反向恢复损耗 Reverse recovery energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	E_{rec}	4.5 8.1		mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0.17	K/W
在开关状态下温度 Temperature under switching			T_{jop}	-40	125	$^\circ\text{C}$

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模块 / Module



绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}	2.5	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘/Internal isolation	基本绝缘 (class 1, IEC 61140) Basic insulation (class1, IEC 61140)		Al_2O_3	
爬电距离/Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		29.0 23.0	mm
电气间隙/Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		23.0 11.0	mm
相对电痕指数 Comperative tracking index		CTI	> 400	

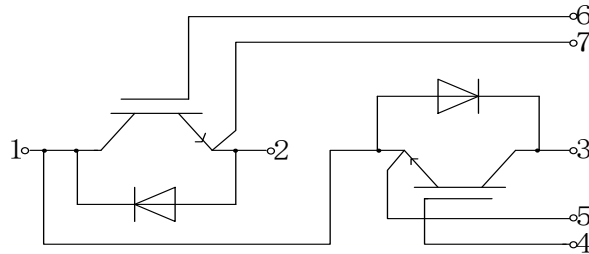
			Min.	Typ.	Max.	
杂散电感, 模块 Stray inductance module		L_{SCE}		20		nH
模块引线电阻 Module lead resistance	$T_c = 25^\circ C$, 每个开关 / per switch	$R_{CC'+EE'}$		0.69		m Ω
储存温度/Storage temperature		T_{stg}	-40		125	$^\circ C$
模块安装的安装扭矩 / Mounting torque for module mounting	螺丝 M6 / Screw M6	M	3.00		6.00	Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 / Screw M6	M	2.5		5.0	Nm
重量/Weight		G		300		g

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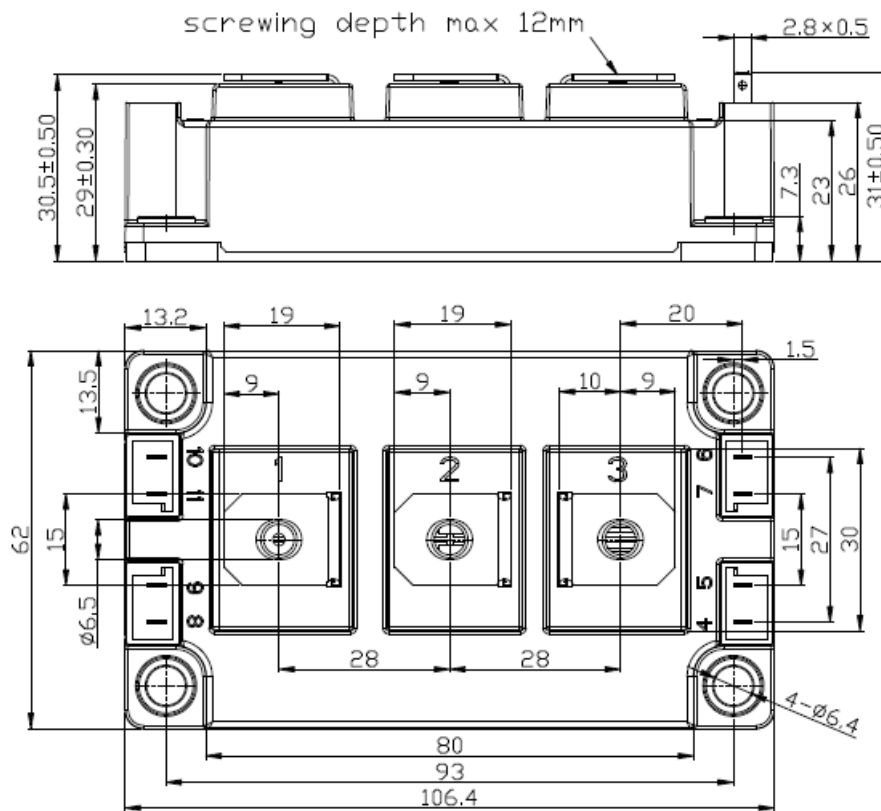


封装 / Package

接线图 / Circuit Diagram



封装尺寸 / Package outlines

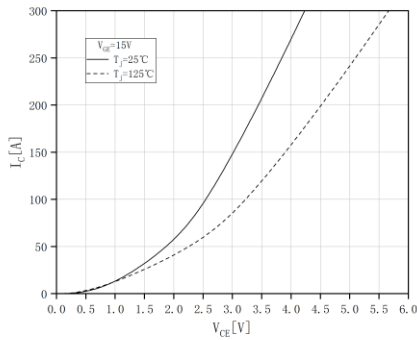


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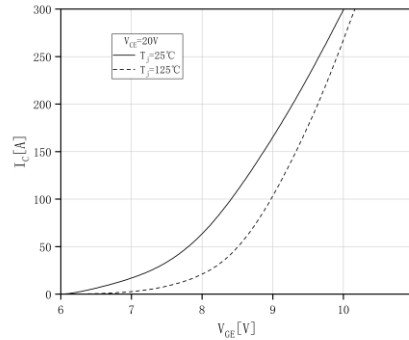
性能 / Performance



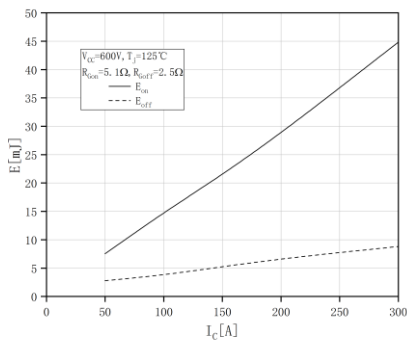
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)



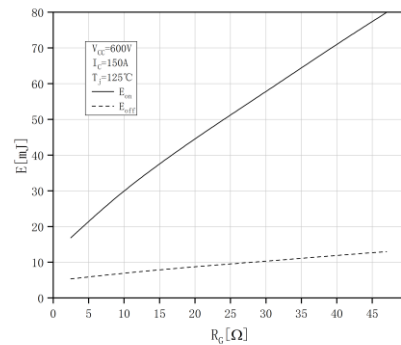
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)



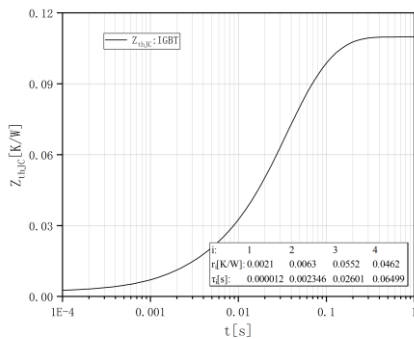
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)



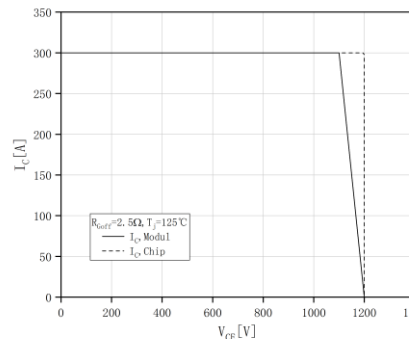
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)



瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter



反偏安全工作区 IGBT, 逆变器 (RBSOA)
Reverse bias safe operating area IGBT, Inverter(RBSOA)

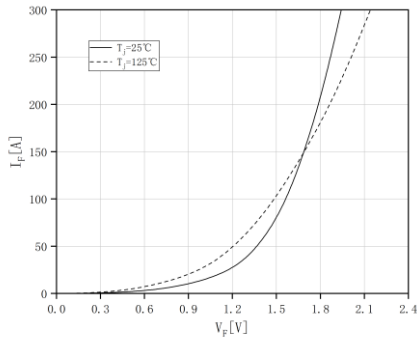


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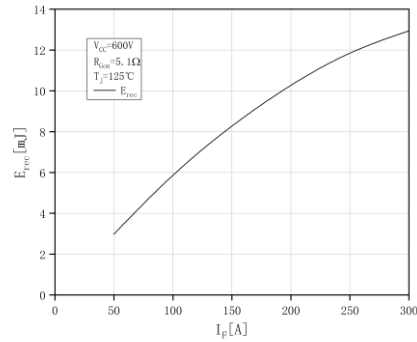
性能 / Performance



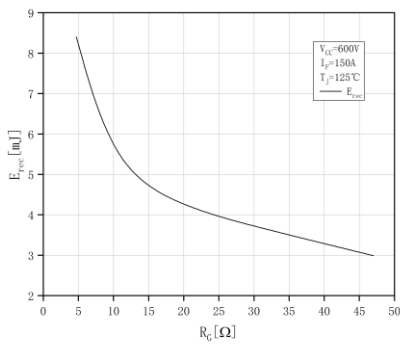
正向偏压特性 二极管,逆变器 (典型)
forward characteristic of Diode, Inverter(typical)



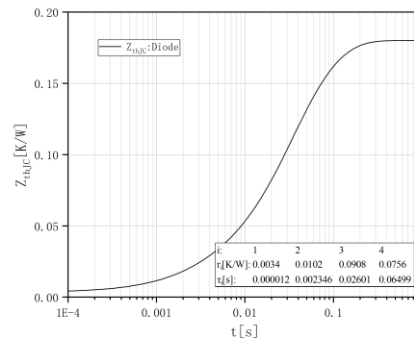
开关损耗 二极管, 逆变器 (典型)
switching losses Diode, Inverter(typical)



开关损耗 二极管, 逆变器 (典型)
switching losses Diode, Inverter(typical)



瞬态热阻抗 二极管, 逆变器
transient thermal impedance Diode, Inverter



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